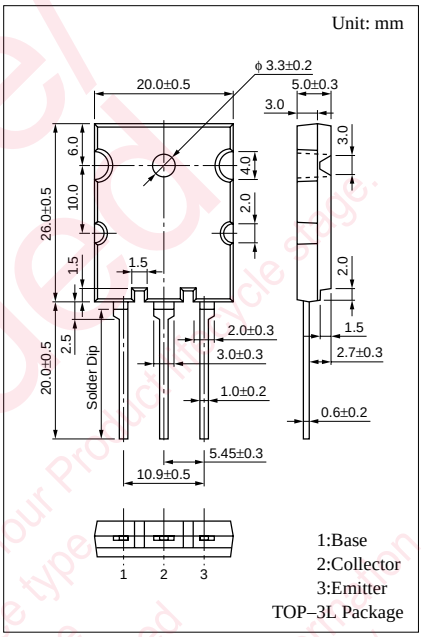
2SC3738

Silicon NPN triple diffusion planar type

For high breakdown voltage high-speed switching
For horizontal deflection output



Features

- High-speed switching
- Wide area of safe operation (ASO) with high breakdown voltage
- Satisfactory linearity of foward current transfer ratio h_{FE}

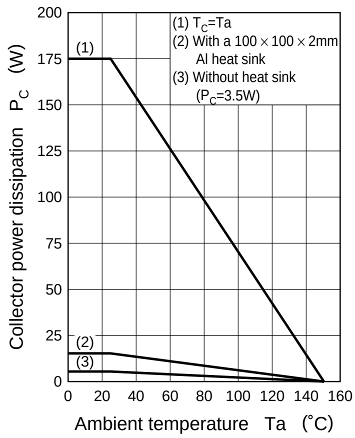
Absolute Maximum Ratings (T_C=25˚C)

Parameter		Symbol	Ratings	Unit
Collector to base voltage		V_{CBO}	1200	V
Collector to emitter voltage		V_{CEO}	800	V
Emitter to base voltage		V_{EBO}	7	V
Peak collector current		I_{CP}	15	A
Collector current		I_C	10	A
Base current		I_B	5	A
Collector power dissipation	T_C=25°C	P_C	175	W
	Ta=25°C		3.5	
Junction temperature		T_j	150	˚C
Storage temperature		T_{stg}	–55 to +150	˚C

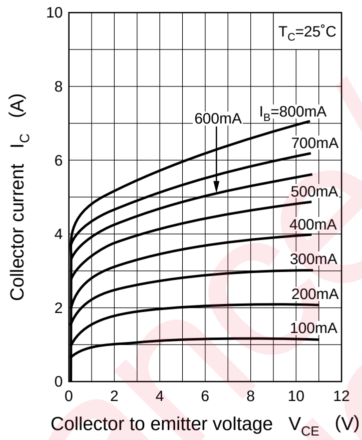
Electrical Characteristics (T_C=25˚C)

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	I_{CBO}	V_{CB} = 1000V, I_E = 0			100	µA
Emitter cutoff current	I_{EBO}	V_{EB} = 6V, I_C = 0			100	µA
Collector to emitter voltage	V_{CEO}	I_C = 10mA, I_B = 0	800			V
Forward current transfer ratio	h_{FE}	V_{CE} = 5V, I_C = 4A	6		20	
Collector to emitter saturation voltage	$V_{CE(sat)}$	I_C = 4A, I_B = 0.8A			1.5	V
Base to emitter saturation voltage	$V_{BE(sat)}$	I_C = 4A, I_B = 0.8A			2.0	V
Transition frequency	f_T	V_{CE} = 5V, I_C = 0.5A, f = 1MHz		10		MHz
Turn-on time	t_{on}	I_C = 4A, I_{B1} = 0.8A, I_{B2} = –1.6A, V_{CC} = 250V			1.0	µs
Storage time	t_{stg}				3.5	µs
Fall time	t_f				0.3	µs

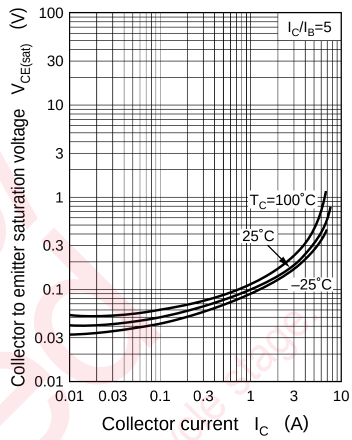
P_C — Ta



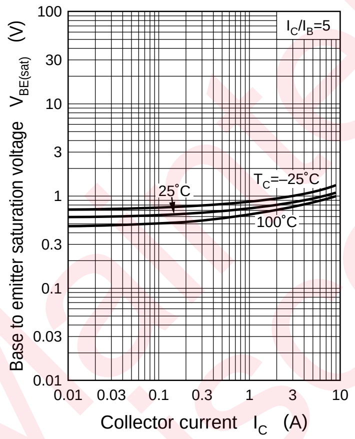
I_C — V_{CE}



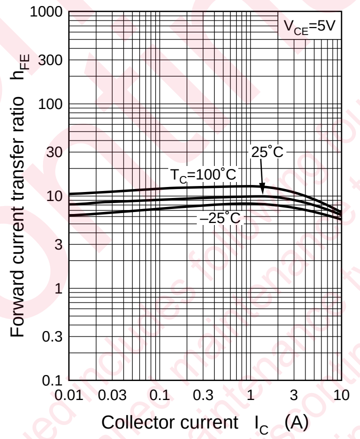
$V_{CE(sat)}$ — I_C



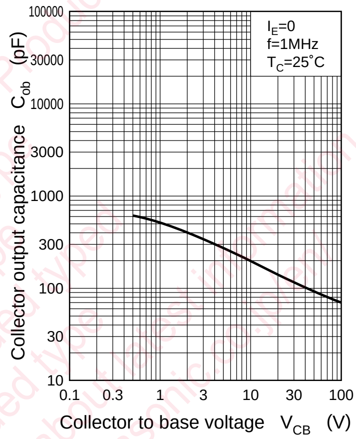
$V_{BE(sat)}$ — I_C



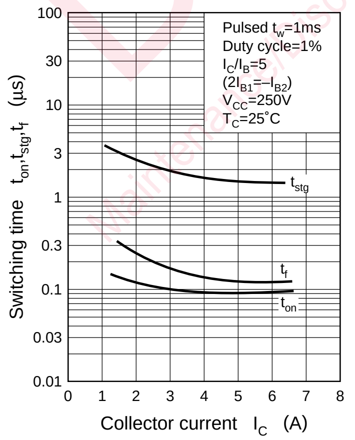
h_{FE} — I_C



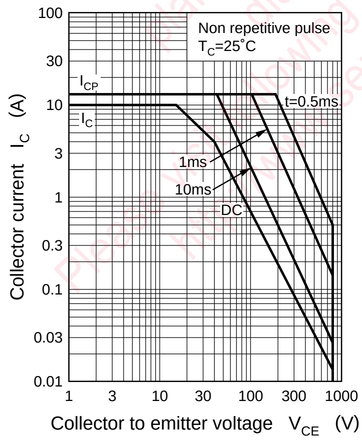
C_{ob} — V_{CB}



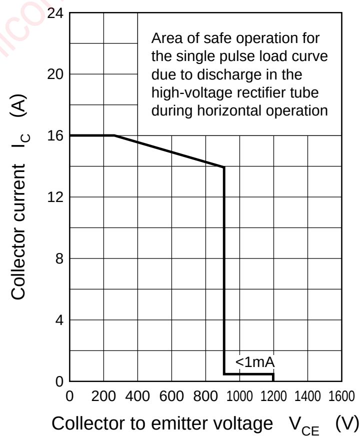
t_{on}, t_{stg}, t_f — I_C



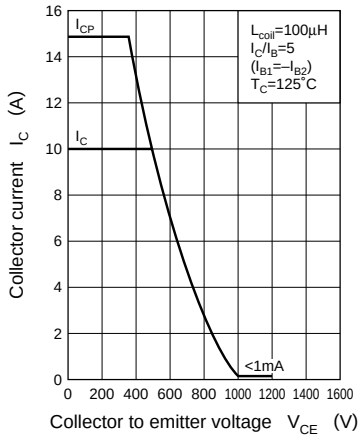
Area of safe operation (ASO)



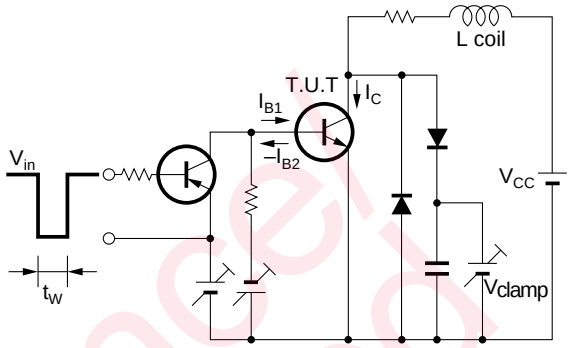
Area of safe operation, horizontal operation ASO



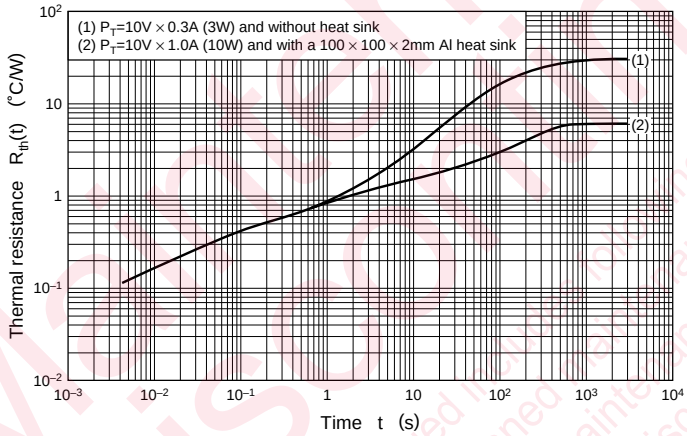
Area of safe operation, reverse bias ASO



Reverse bias ASO measuring circuit



$R_{th(t)}$ — t



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